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Low-power dual buffer and single inverter Rev. 1 — 14 January 2013

Product data sheet

General description 1.

The 74AUP3G3404 is a dual buffer and single inverter.

Schmitt trigger action at all inputs makes the circuit tolerant of slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using IOFF. The IOFF circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

Features and benefits 2.

- Wide supply voltage range from 0.8 V to 3.6 V
- High noise immunity
- Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - ◆ JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; $I_{CC} = 0.9 \ \mu A$ (maximum)
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering i	nformation							
Type number	Package							
	Temperature range Name		Description	Version				
74AUP3G3404DC	–40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				
74AUP3G3404GT	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $1 \times 1.95 \times 0.5$ mm	SOT833-1				
74AUP3G3404GF	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1 \times 0.5$ mm	SOT1089				
74AUP3G3404GD	–40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body $3 \times 2 \times 0.5$ mm	SOT996-2				
74AUP3G3404GM	–40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body $1.6 \times 1.6 \times 0.5$ mm	SOT902-2				
74AUP3G3404GN	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.2 \times 1.0 \times 0.35$ mm	SOT1116				
74AUP3G3404GS	–40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body $1.35 \times 1.0 \times 0.35$ mm	SOT1203				

4. Marking

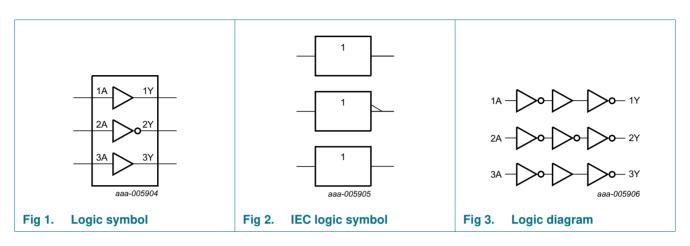
Table 2.Marking codes

Type number	Marking code ^[1]
74AUP3G3404DC	aZ
74AUP3G3404GT	aZ
74AUP3G3404GF	aZ
74AUP3G3404GD	aZ
74AUP3G3404GM	aZ
74AUP3G3404GN	aZ
74AUP3G3404GS	aZ

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

Low-power dual buffer and single inverter

Functional diagram 5.

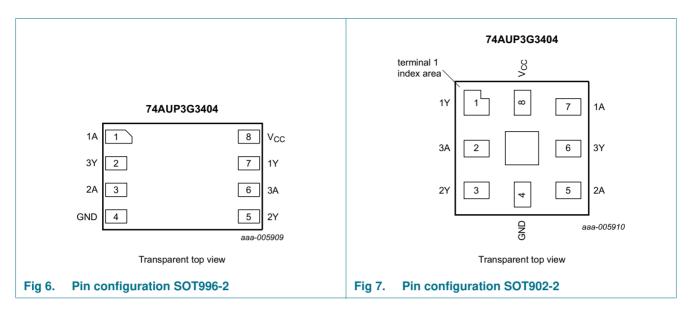


Pinning information 6.

74AUP3G3404 1 8 1A V_{CC} 7 3Y 2 1Y 74AUP3G3404 3 6 ЗA 2A 1A 1 8 V_{CC} 3Y 2 7 1Y GND 4 5 2Y 6 3A 2A 3 5 2Y GND 4 aaa-005907 aaa-005908 Transparent top view Pin configuration SOT765-1 Pin configuration SOT833-1, SOT1089, Fig 4. Fig 5. SOT1116 and SOT1203

6.1 Pinning

Low-power dual buffer and single inverter



6.2 Pin description

Symbol	Pin	Description				
	SOT765-1, SOT833-1, SOT1089, SOT996-2, SOT1116 and SOT1203	SOT902-2				
1A, 2A, 3A	1, 3, 6	7, 5, 2	data input			
1Y, 2Y, 3Y	7, 5, 2	1, 3, 6	data output			
GND	4	4	ground (0 V)			
V _{CC}	8	8	supply voltage			

7. Functional description

Table 4. Function table^[1]

_. .

Input 1A, 3A	Output
1A, 3A	1Y, 3Y
L	L
Н	Н

[1] H = HIGH voltage level; L = LOW voltage level.

Table 5.Function table

Input	Output
2A	2Y
L	Н
Н	L

[1] H = HIGH voltage level; L = LOW voltage level.

8. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Мах	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage		<u>[1]</u> –0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode	<u>[1]</u> –0.5	+4.6	V
lo	output current	$V_{\rm O} = 0$ V to $V_{\rm CC}$	-	±20	mA
I _{CC}	supply current		-	50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +125 \ ^{\circ}C$	[2] _	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly with 8.0 mW/K. For XSON8 and XQFN8 packages: above 118 °C the value of P_{tot} derates linearly with 7.8 mW/K.

9. Recommended operating conditions

Table 7.Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		0.8	3.6	V
VI	input voltage		0	3.6	V
Vo	output voltage	Active mode	0	V _{CC}	V
		Power-down mode; $V_{CC} = 0 V$	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
$\Delta t / \Delta V$	input transition rise and fall rate	$V_{CC} = 0.8 V$ to 3.6 V	-	200	ns/V

10. Static characteristics

Table 8. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	5 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	0.70V _{CC}	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	$0.65V_{CC}$	-	-	V
		$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35V_{CC}$	V
		$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
V _{OH}	HIGH-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_O = –20 $\mu A;V_{CC}$ = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.75V _{CC}	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.11	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.32	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	2.05	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.72	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.6	-	-	V
V _{OL}	LOW-level output voltage	$V_I = V_{IH} \text{ or } V_{IL}$				
		I_O = 20 $\mu A; V_{CC}$ = 0.8 V to 3.6 V	-	-	0.1	V
		$I_{O} = 1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	-	-	0.3V _{CC}	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.31	V
		$I_{O} = 1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.31	V
		$I_{O} = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.31	V
		$I_{O} = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.44	V
		I_{O} = 2.7 mA; V_{CC} = 3.0 V	-	-	0.31	V
		I_{O} = 4.0 mA; V_{CC} = 3.0 V	-	-	0.44	V
	input leakage current	$V_{\rm I}$ = GND to 3.6 V; $V_{\rm CC}$ = 0 V to 3.6 V	-	-	±0.1	μA
OFF	power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μA
Δl _{OFF}	additional power-off leakage current	V_1 or $V_O = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μA
lcc	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \text{ to } 3.6 \ V \end{array}$	-	-	0.5	μA
Δl _{CC}	additional supply current		-	-	40	μA
CI	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	1.0	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	1.8	-	pF

Low-power dual buffer and single inverter

Table 8. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input voltage	$V_{CC} = 0.8 V$	0.70V _{CC}	-	-	V
		$V_{CC} = 0.9 \text{ V}$ to 1.95 V	$0.65V_{CC}$	-	-	V
		V_{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
V _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.30V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.35V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	$V_{CC}-0.1$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.7V _{CC}	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	1.03	-	-	V
		I _O = −1.9 mA; V _{CC} = 1.65 V	1.30	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.97	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.85	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.67	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.55	-	-	V
V _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
-		$I_{O} = 20 \ \mu$ A; $V_{CC} = 0.8 \ V$ to 3.6 V	-	-	0.1	V
		l _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		$I_0 = 1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.33	V
		$I_0 = 3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.45	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.33	V
		$I_{O} = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.45	V
I	input leakage current	$V_{I} = GND \text{ to } 3.6 \text{ V}; V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μA
OFF	power-off leakage current	$V_{\rm I}$ or $V_{\rm O} = 0$ V to 3.6 V; $V_{\rm CC} = 0$ V	-	-	±0.5	μΑ
	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.6	μΑ
сс	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	0.9	μA
∆l _{CC}	additional supply current		-	-	50	μA

Low-power dual buffer and single inverter

Table 8. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Uni
T _{amb} = -	40 °C to +125 °C					
ViH	HIGH-level input voltage	$V_{CC} = 0.8 V$	0.75V _{CC}	-	-	V
		$V_{CC} = 0.9 V$ to 1.95 V	0.70V _{CC}	-	-	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.6	-	-	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	-	-	V
/ _{IL}	LOW-level input voltage	$V_{CC} = 0.8 V$	-	-	$0.25V_{CC}$	V
		$V_{CC} = 0.9 V$ to 1.95 V	-	-	$0.30V_{CC}$	V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	-	-	0.7	V
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	-	-	0.9	V
/ _{ОН}	HIGH-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		I_{O} = –20 $\mu A;$ V_{CC} = 0.8 V to 3.6 V	$V_{CC} - 0.11$	-	-	V
		$I_{O} = -1.1 \text{ mA}; V_{CC} = 1.1 \text{ V}$	0.6V _{CC}	-	-	V
		$I_{O} = -1.7 \text{ mA}; V_{CC} = 1.4 \text{ V}$	0.93	-	-	V
		$I_{O} = -1.9 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.17	-	-	V
		$I_{O} = -2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.77	-	-	V
		$I_{O} = -3.1 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.67	-	-	V
		$I_{O} = -2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.40	-	-	V
		$I_{O} = -4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.30	-	-	V
/ _{OL}	LOW-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$				
		$I_{O} = 20 \ \mu A; V_{CC} = 0.8 \ V \text{ to } 3.6 \ V$	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		$I_0 = 2.3 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		$I_0 = 2.7 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.36	V
		$I_0 = 4.0 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.50	V
1	input leakage current	$V_{I} = GND$ to 3.6 V; $V_{CC} = 0$ V to 3.6 V	-	-	±0.75	μA
OFF	power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±0.75	μA
I _{OFF}	additional power-off leakage current	$V_{I} \text{ or } V_{O} = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 0.2 \text{ V}$	-	-	±0.75	μA
CC	supply current	$\label{eq:VI} \begin{array}{l} V_{I} = GND \text{ or } V_{CC}; \ I_{O} = O \ A; \\ V_{CC} = 0.8 \ V \ to \ 3.6 \ V \end{array}$	-	-	1.4	μ A
VI _{CC}	additional supply current		-	-	75	μA

11. Dynamic characteristics

Table 9. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C		-40	0 °C to +1	25 °C	Unit
			Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	_
C _L = 5 pl	F								
t _{pd}	propagation delay	nA to nY; see Figure 8 [2]							
		$V_{CC} = 0.8 V$	-	16.0	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V}$ to 1.3 V	2.4	5.0	10.3	2.0	11.4	12.6	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	1.8	3.6	6.4	1.6	7.4	8.2	ns
		$V_{CC} = 1.65 \text{ V}$ to 1.95 V	1.5	2.9	5.0	1.4	5.9	6.5	ns
		V_{CC} = 2.3 V to 2.7 V	1.2	2.4	3.9	1.1	4.5	5.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.1	2.1	3.2	1.0	3.9	4.3	ns
C _L = 10 J	pF								
t _{pd}	propagation delay	nA to nY; see Figure 8 [2]							
		$V_{CC} = 0.8 V$	-	19.8	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	2.8	5.9	12.2	2.3	13.7	15.1	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	2.3	4.2	7.5	1.9	8.7	9.6	ns
		$V_{CC} = 1.65 \text{ V}$ to 1.95 V	2.0	3.5	5.9	1.7	7.0	7.7	ns
		$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	1.7	2.9	4.6	1.5	5.4	6.0	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.6	2.7	3.8	1.4	4.5	5.1	ns
C _L = 15 J	pF								
t _{pd}	propagation delay	nA to nY; see Figure 8 [2]							
		$V_{CC} = 0.8 V$	-	23.3	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V to } 1.3 \text{ V}$	3.2	6.7	13.0	2.6	15.8	17.4	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	2.6	4.7	8.6	2.2	10.0	11.0	ns
		$V_{CC} = 1.65 \text{ V} \text{ to } 1.95 \text{ V}$	2.3	4.0	6.7	2.0	8.0	8.8	ns
		$V_{CC} = 2.3 \text{ V} \text{ to } 2.7 \text{ V}$	2.1	3.3	5.1	1.8	6.1	6.8	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	2.0	3.1	4.2	1.6	5.0	5.5	ns
C _L = 30	pF								
t _{pd}	propagation delay	nA to nY; see Figure 8 [2]							
		$V_{CC} = 0.8 V$	-	33.6	-	-	-	-	ns
		$V_{CC} = 1.1 \text{ V}$ to 1.3 V	4.4	8.9	16.3	3.6	19.0	20.9	ns
		$V_{CC} = 1.4 \text{ V}$ to 1.6 V	3.6	6.3	10.8	3.2	12.9	14.2	ns
		$V_{CC} = 1.65 \text{ V}$ to 1.95 V	3.2	5.3	9.0	2.9	10.5	11.6	ns
		V_{CC} = 2.3 V to 2.7 V	2.9	4.5	6.5	2.6	7.6	8.5	ns
		$V_{CC} = 3.0 V \text{ to } 3.6 V$	2.9	4.2	5.6	2.5	6.2	7.2	ns

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Table 9. Dynamic characteristics ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 9.

Symbol	Parameter	Conditions		25 °C			-40	Unit		
				Min	Typ <mark>[1]</mark>	Мах	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 pl	F, 10 pF, 15 pF and	30 pF								
C _{PD}	power dissipation capacitance	$f_i = 1 \text{ MHz}; V_I = \text{GND to } V_{\text{CC}}$	[3][4]							
		$V_{CC} = 0.8 V$		-	2.5	-	-	-	-	pF
		V _{CC} = 1.1 V to 1.3 V		-	2.7	-	-	-	-	pF
		$V_{CC} = 1.4 \text{ V} \text{ to } 1.6 \text{ V}$		-	2.8	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V		-	3.0	-	-	-	-	pF
		V_{CC} = 2.3 V to 2.7 V		-	3.5	-	-	-	-	pF
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$		-	4.0	-	-	-	-	pF

[1] All typical values are measured at nominal $V_{\text{CC}}.$

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] All specified values are the average typical values over all stated loads.

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_{D} = C_{PD} \times V_{CC}^{2} \times f_{i} \times N + \Sigma(C_{L} \times V_{CC}^{2} \times f_{o}) \text{ where:}$

f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

12. Waveforms

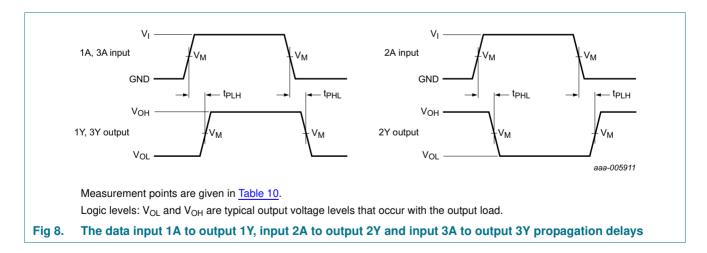


Table 10.Measurement points

Supply voltage	Output	Input		
V _{CC}	V _M	V _M	VI	t _r = t _f
0.8 V to 3.6 V	0.5V _{CC}	0.5V _{CC}	V _{CC}	≤ 3.0 ns

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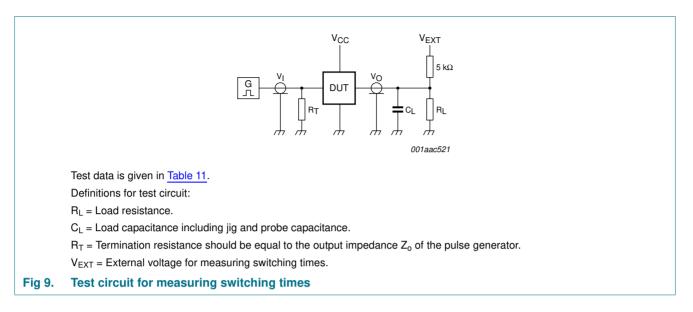


Table 11. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF, and 30 pF	5 k Ω or 1 M Ω	open	GND	2V _{CC}

[1] For measuring enable and disable times, $R_L = 5 k\Omega$.

For measuring propagation delays, setup and hold times, and pulse width, $R_L = 1 M\Omega$.

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13. Package outline

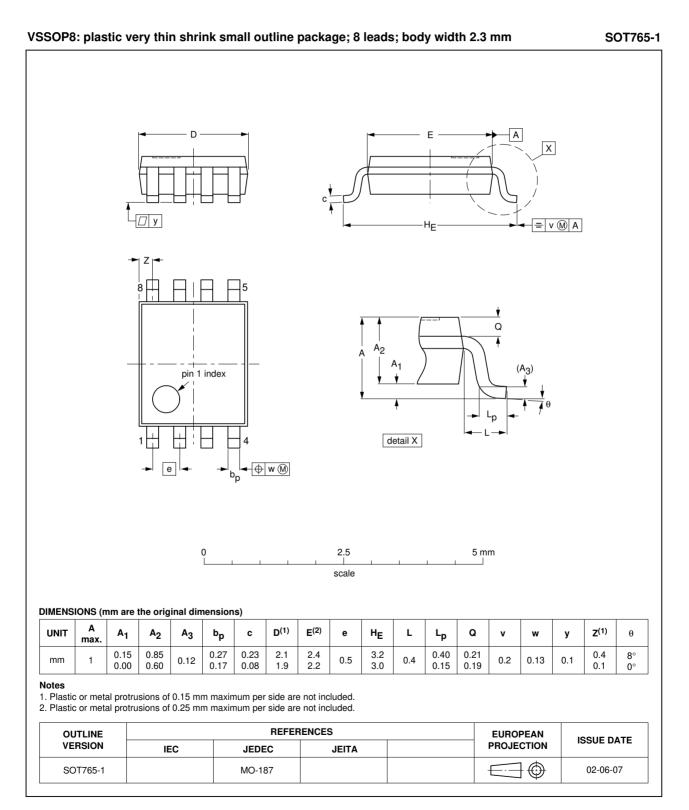


Fig 10. Package outline SOT765-1 (VSSOP8)

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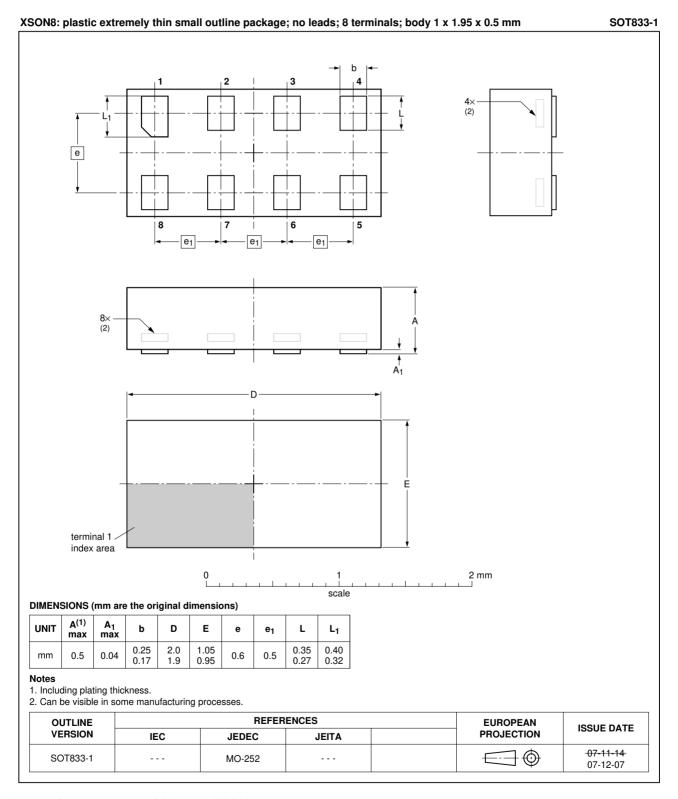


Fig 11. Package outline SOT833-1 (XSON8)

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XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1 x 0.5 mm

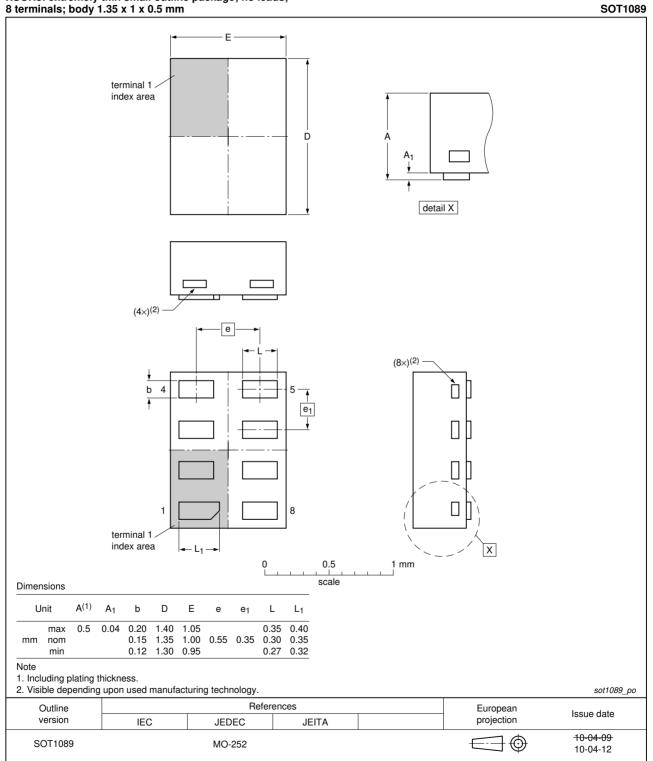
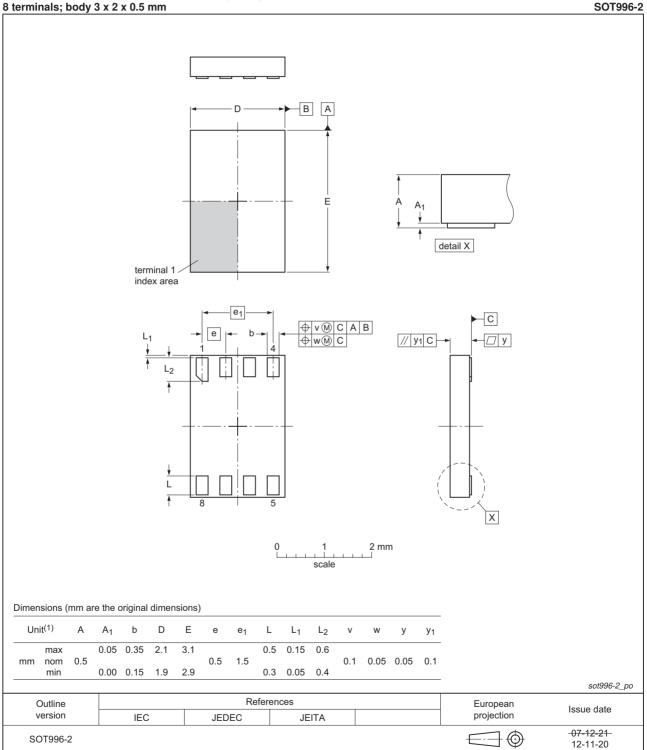


Fig 12. Package outline SOT1089 (XSON8)

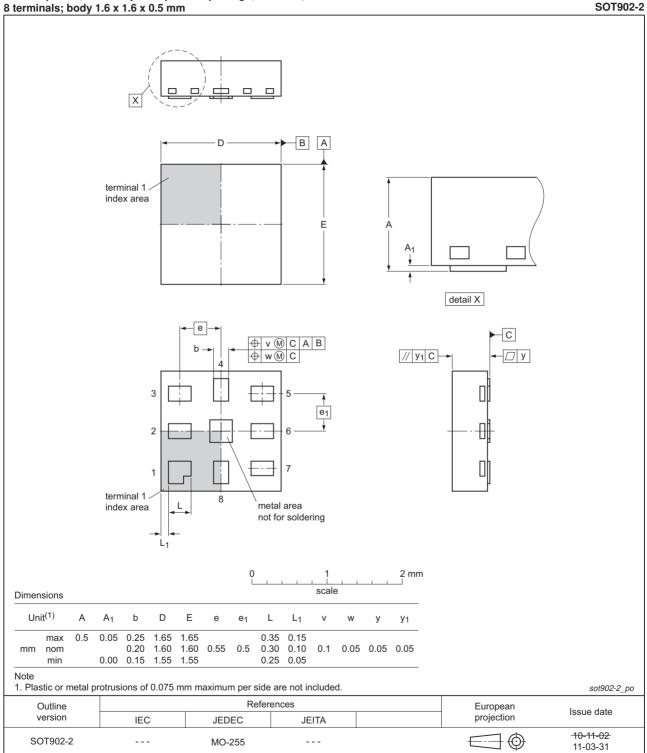
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XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 3 x 2 x 0.5 mm

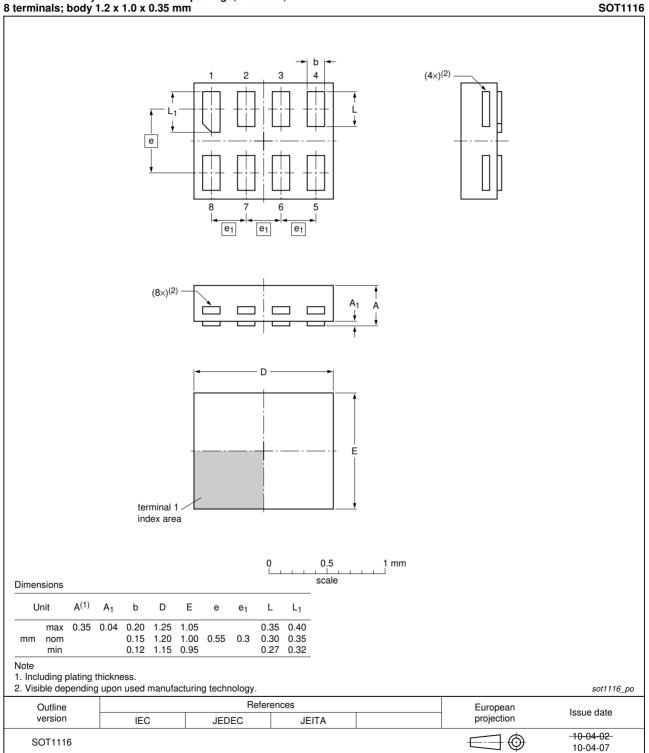
Fig 13. Package outline SOT996-2 (XSON8)

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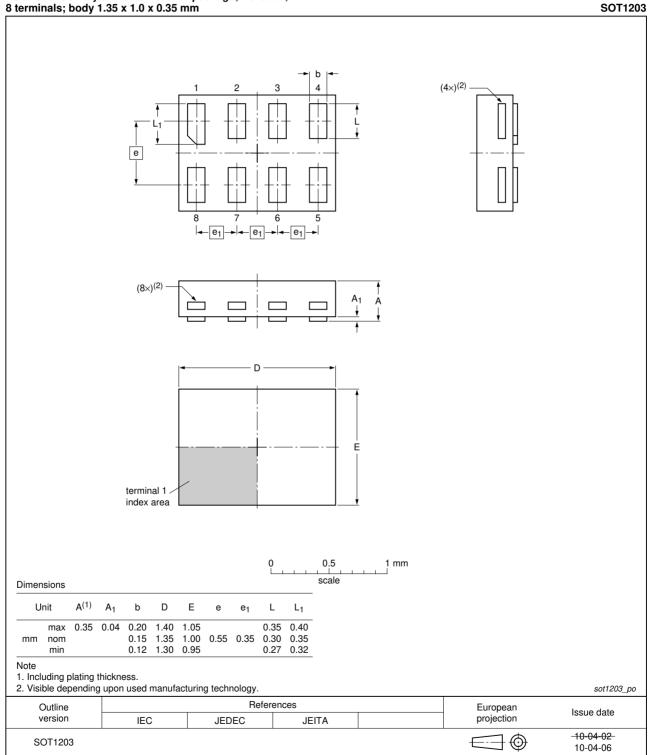
XQFN8: plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 x 1.6 x 0.5 mm

Fig 14. Package outline SOT902-2 (XQFN8)



XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.2 x 1.0 x 0.35 mm

Fig 15. Package outline SOT1116 (XSON8)



XSON8: extremely thin small outline package; no leads; 8 terminals; body 1.35 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1203 (XSON8)

14. Abbreviations

Table 12.	Abbreviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model

15. Revision history

Table 13. Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes
74AUP3G3404 v.1	20130114	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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